30 V, 2 A ultra low V_F MEGA Schottky barrier rectifiers

Rev. 04 — 4 February 2010 Product de

Product data sheet

1. **Product profile**

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection encapsulated in small SMD plastic packages.

Table 1. **Product overview**

Type number	Package		Configuration	
	NXP	JEITA		
PMEG3020EH	SOD123F	-	single isolated diodes	
PMEG3020EJ	SOD323F	SC-90	single isolated diodes	

1.2 Features

Forward current: 2 A

Reverse voltage: 30 V

Ultra low forward voltage

Small and flat lead SMD package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switched-mode power supply
- Inverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 2. Quick reference data

I_F forward current $T_{sp} \le 55 ^{\circ} C$ 2 A	
V _R reverse voltage 30 V	
V_F forward voltage $I_F = 2000 \text{ mA}$ [1] - 510 620 m	ıV

^[1] Pulse test: $t_0 \le 300 \ \mu s; \ \delta \le 0.02$.



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2. Pinning information

Table 3. Pinning

	3	
Pin	Description	Simplified outline Symbol
1	cathode	<u>[1]</u>
2	anode	1 2
		001aab540

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
PMEG3020EH	-	plastic surface mounted package; 2 leads	SOD123F		
PMEG3020EJ	SC-90	plastic surface mounted package; 2 leads	SOD323F		

4. Marking

Table 5. Marking codes

Type number	Marking code
PMEG3020EH	A7
PMEG3020EJ	E9

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5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

			-		
Symbol	Parameter	Conditions	Min	Max	Unit
V_{R}	reverse voltage		-	30	V
I _F	forward current	T _{sp} ≤ 55 °C	-	2	Α
I _{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ ms; } \delta \leq 0.25$	-	4.5	Α
I _{FSM}	non-repetitive peak forward current	t = 8 ms; square wave	<u>[1]</u> _	9	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PMEG3020EH		<u>[1]</u> _	375	mW
			[2] _	830	mW
	PMEG3020EJ		<u>[1]</u> _	360	mW
			[2] _	830	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air					
	PMEG3020EH		[1][2]	-	-	330	K/W
			[2][3]	-	-	150	K/W
	PMEG3020EJ		[1][2]	-	-	350	K/W
			[2][3]	-	-	150	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point						
	PMEG3020EH			-	-	60	K/W
	PMEG3020EJ			-	-	55	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1cm².

^[2] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and I_{F(AV)} rating will be available on request.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1cm².

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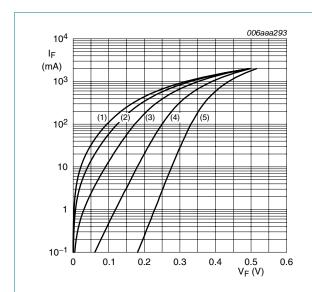
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>			
		I _F = 1 mA	-	125	160	mV
		I _F = 10 mA	-	185	220	mV
		I _F = 100 mA	-	255	290	mV
		$I_F = 500 \text{ mA}$	-	330	380	mV
		I _F = 1000 mA	-	400	480	mV
		I _F = 2000 mA	-	510	620	mV
I _R	reverse current	V _R = 10 V	-	60	150	μΑ
		V _R = 30 V	-	400	1000	μΑ
C _d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$	-	60	72	рF

[1] Pulse test: $t_0 \le 300 \ \mu s; \ \delta \le 0.02$.

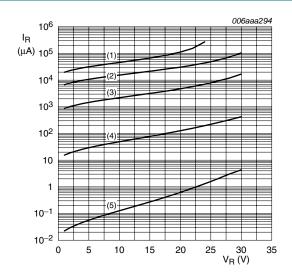




⁽²⁾ $T_{amb} = 125 \, ^{\circ}C$

(5) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



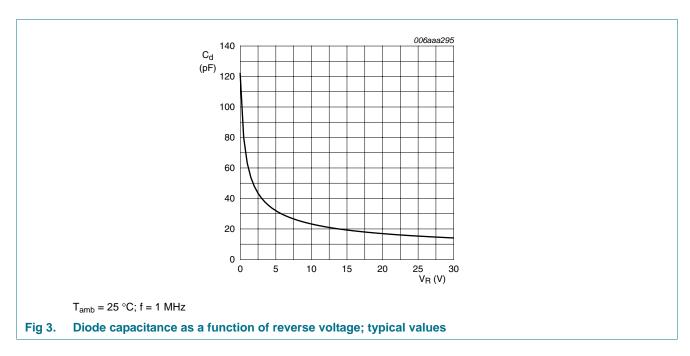
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) T_{amb} = 25 °C
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values

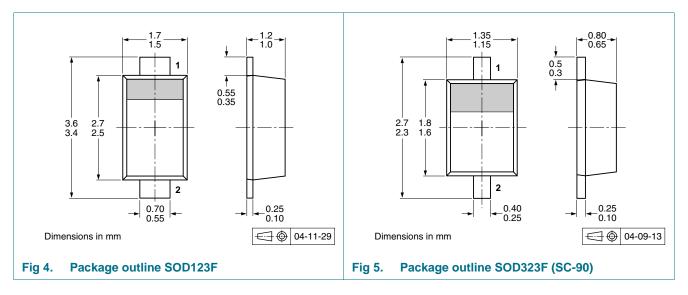
⁽³⁾ $T_{amb} = 85 \, ^{\circ}C$

⁽⁴⁾ $T_{amb} = 25 \, ^{\circ}C$

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8. Package outline



9. Packing information

Table 9. Packing methods

The -xxx numbers are the last three digits of the 12NC ordering code.[1]

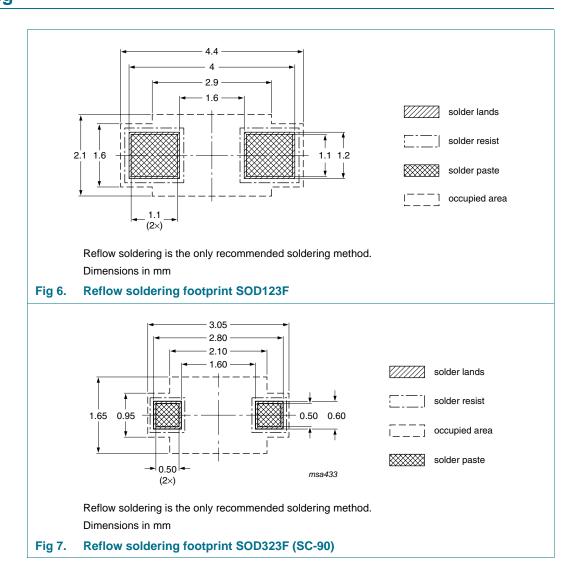
Type number	Package	Description	Packing quantity	
			3000	10000
PMEG3020EH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135
PMEG3020EJ	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see Section 13.

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10. Soldering



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11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3020EH_EJ_4	20100204	Product data sheet	-	PMEG3020EH_EJ_3
Modifications:		et was changed to reflect to legal definitions and discl		
PMEG3020EH_EJ_3	20050531	Product data sheet	-	PMEG3020EH_EJ_2
PMEG3020EH_EJ_2	20050404	Product data sheet	-	PMEG3020EJ_1
PMEG3020EJ_1	20050125	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PMEG3020EH; PMEG3020EJ

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